Abstracts

On-Wafer Verification of a Large-Signal MESFET Model (Short Papers)

W.R. Curtice and S. Pak. "On-Wafer Verification of a Large-Signal MESFET Model (Short Papers)." 1989 Transactions on Microwave Theory and Techniques 37.11 (Nov. 1989 [T-MTT]): 1809-1811.

A relatively simple and new RF measurement procedure is described that is useful for on-wafer, large-signal tests. Predictions using the GaAs FET model agree well with measurements of typical RF gain, gain compression at the fundamental frequency, and the power output at the second and third harmonics.

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